FMS SOT-23 Plastic-Encapsulate Transistors

MMBT3906 TRANSISTOR (PNP)

FEATURES

- As complementary type, the NPN transistor MMBT3904 is Recommended
- Epitaxial planar die construction



MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current -Continuous	-0.2	Α
Pc	Collector Power Dissipation	0.3	W
TJ	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -10μA,I _E =0	-40		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, I _B =0	-40		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} = -40V, _E =0		-0.1	μΑ
Collector cut-off current	I _{CEX}	V_{CE} =-30V, $V_{BE(off)}$ =-3V		-50	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0		-0.1	μΑ
	h _{FE(1)}	V _{CE} =-1V, I _C =-10mA	100	300	
DC current gain	h _{FE(2)}	V _{CE} = -1V, I _C =-50mA	60		
	h _{FE(3)}	V _{CE} = -1V, I _C =-100mA	30		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-50mA, I _B =-5mA		-0.4	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =- 50mA, I _B =- 5mA		-0.95	>
Transition frequency	f _T	V _{CE} =-20V, I _C =-10mA, f=100MHz	250		MHz
Delay Time	t _d	V _{CC} =-3.0V,V _{BE} =-0.5V		35	nS
Rise Time	t _r	I _C =-10mA,I _{B1} =-1.0mA		35	nS
Storage Time	ts	V _{CC} =-3.0V,I _C =-10mA		225	nS
Fall Time	t _f	I _{B1} =I _{B2} =-1.0mA		75	nS

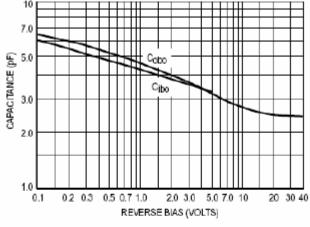
CLASSIFICATION OF h_{FE1}

Rank	0	Y
Range	100-200	200-300



Typical Characteristics

MMBT3906





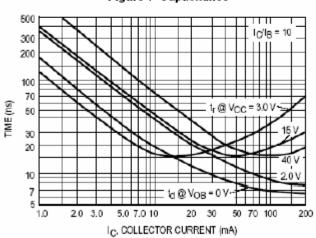


Figure 3 Turn-On Time

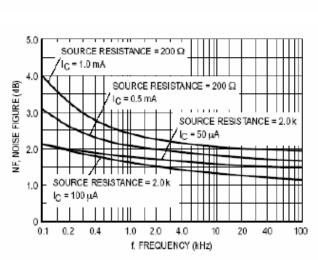


Figure 5

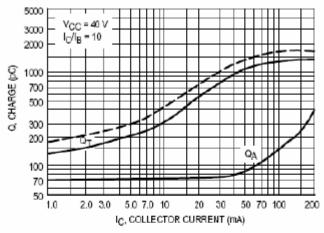


Figure 2 Charge Data

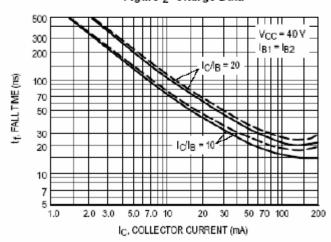


Figure 4 Fall Time

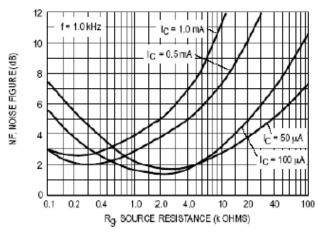


Figure 6

h PARAMETERS

(VCE = -10 Vdc, f = 1.0 kHz, TA = 25°C)

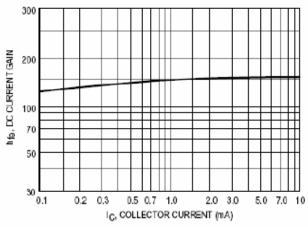


Figure 7 Current Gain

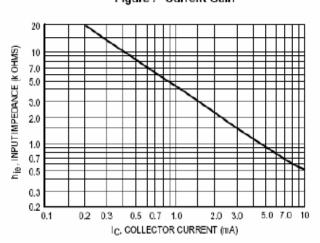


Figure 9 Input Impedance

VCE(sat) © IC/IS = 10

1.0 2.0 5.0 10 20 50 100 200

IC COLLECTOR CURRENT (mA)

Figure 11 "ON" Voltages

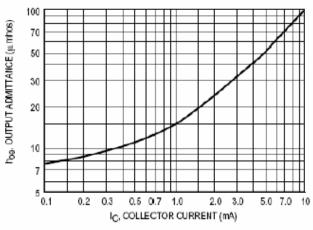
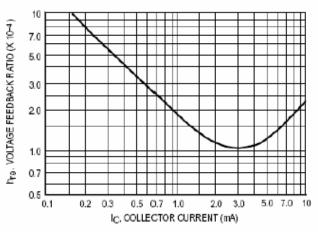


Figure 8 Output Admittance



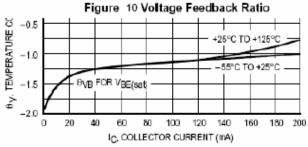


Figure 12 Temperature Coefficients